

Data Sheet

September 2013

N-Channel Power MOSFET 50V, 14A, 100 $m\Omega$

These are N-channel power MOSFETs manufactured using the MegaFET process. This process, which uses feature sizes approaching those of LSI integrated circuits, gives optimum utilization of silicon, resulting in outstanding performance. They were designed for use in applications such as switching regulators, switching converters, motor drivers and relay drivers. These transistors can be operated directly from integrated circuits.

Formerly developmental type TA09770.

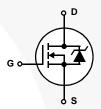
Ordering Information

PART NUMBER	PACKAGE	BRAND			
RFD14N05SM9A	TO-252AA	F14N05			

Features

- 14A, 50V
- $r_{DS(ON)} = 0.100\Omega$
- Temperature Compensating PSPICE[®] Model
- Peak Current vs Pulse Width Curve
- · UIS Rating Curve
- 175°C Operating Temperature
- · Related Literature
 - TB334 "Guidelines for Soldering Surface Mount Components to PC Boards"

Symbol



Packaging

JEDEC TO-252AA



RFD14N05SM9A

Absolute Maximum Ratings $T_C = 25^{\circ}C$, Unless Otherwise Specified

	RFD14N05SM9A	UNITS
Drain to Source Voltage (Note 1)	50	V
Drain to Gate Voltage ($R_{GS} = 20k\Omega$) (Note 1)	50	V
Gate to Source Voltage	±20	V
Continuous Drain Current	14	Α
Pulsed Drain Current (Note 3)	Refer to Peak Current Curve	
Pulsed Avalanche Rating EAS	Refer to UIS Curve	
Power Dissipation	48	W
Derate above 25°C	0.32	W/oC
Operating and Storage Temperature	-55 to 175	°C
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10sT _L	300	°C
Package Body for 10s, See Techbrief 334	260	oC

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. $T_J = 25^{\circ}C$ to $150^{\circ}C$.

Electrical Specifications $T_C = 25^{\circ}C$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	BV _{DSS}	$I_D = 250\mu A, V_{GS} = 0V \text{ (Figure 9)}$		50	-	-	V
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$		2	-	4	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = Rated BV _{DSS} , V _{GS} = 0V		-	-	25	μΑ
		V _{DS} = 0.8 x Rated BV _{DSS}	$V_{GS} = 0V, T_{C} = 150^{\circ}C$	-	-	250	μΑ
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±20V		-	-	±100	nA
Drain to Source On Resistance (Note 2)	r _{DS(ON)}	I _D = 14A, V _{GS} = 10V, (Fig	gure 11)	-	-	0.100	Ω
Turn-On Time	ton	$V_{DD} = 25V, I_{D} \approx 14A, V_{GS} = 10V,$ $R_{GS} = 25\Omega, R_{L} = 1.7\Omega$ (Figure 13)		-	-	60	ns
Turn-On Delay Time	t _d (ON)			-	14	-	ns
Rise Time	t _r			-	26	-	ns
Turn-Off Delay Time	t _d (OFF)			-	45	-	ns
Fall Time	t _f			-	17	-	ns
Turn-Off Time	tOFF			/ -	-	100	ns
Total Gate Charge	Q _{g(TOT)}	$V_{GS} = 0V \text{ to } 20V$	$V_{DD} = 40V, I_D = 14A,$	-	-	40	nC
Gate Charge at 5V	Q _{g(10)}	$ \begin{array}{c c} V_{GS} = 0V \text{ to } 10V \\ \hline V_{GS} = 0V \text{ to } 2V \\ \hline \end{array} \begin{array}{c} R_L = 2.86\Omega \\ I_{g(REF)} = 0.4\text{mA} \\ \text{(Figure 13)} \end{array} $	-	-	25	nC	
Threshold Gate Charge	Q _{g(TH)}		-	-	1.5	nC	
Input Capacitance	C _{ISS}	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz (Figure 12)		-	570	-	pF
Output Capacitance	Coss			-	185	-	pF
Reverse Transfer Capacitance	C _{RSS}			-	50	-	pF
Thermal Resistance Junction to Case	$R_{\theta JC}$			-	-	3.125	oC/W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$			-	-	100	°C/W

Source to Drain Diode Specifications

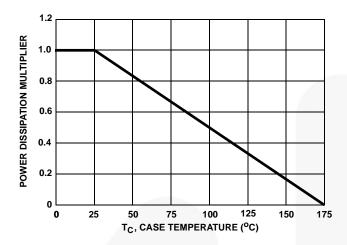
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage (Note 2)	V_{SD}	I _{SD} = 14A	-	-	1.5	V
Diode Reverse Recovery Time	t _{rr}	$I_{SD} = 14A$, $dI_{SD}/dt = 100A/\mu s$	-	-	125	ns

NOTES:

- 2. Pulse Test: Pulse Width ≤300ms, Duty Cycle ≤2%.
- 3. Repetitive Rating: Pulse Width limited by max junction temperature. See Transient Thermal Impedance Curve (Figure 3) and Peak Current Capability Curve (Figure 5).

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Typical Performance Curves Unless Otherwise Specified



16 (e) 12 8 8 0 25 50 75 100 125 150 175 T_C, CASE TEMPERATURE (°C)

FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

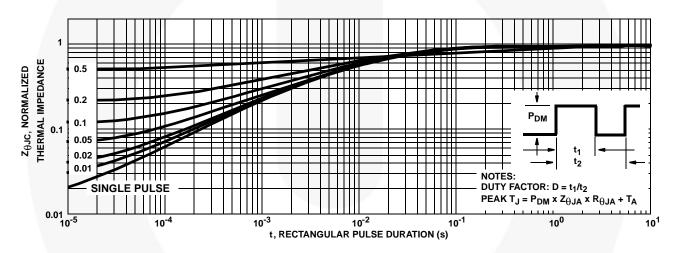


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

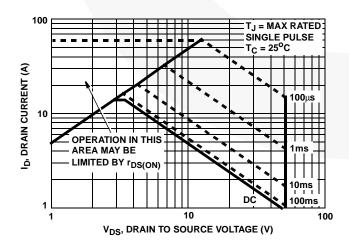


FIGURE 4. FORWARD BIAS SAFE OPERATING AREA

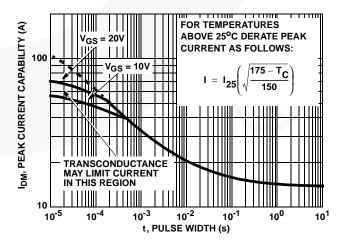
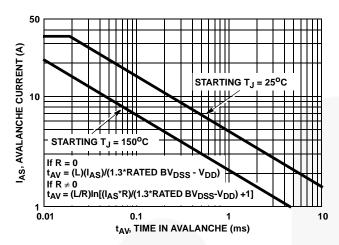


FIGURE 5. PEAK CURRENT CAPABILITY

Typical Performance Curves Unless Otherwise Specified (Continued)



NOTE: Refer to Fairchild Application Notes AN9321 and AN9322.

FIGURE 6. UNCLAMPED INDUCTIVE SWITCHING

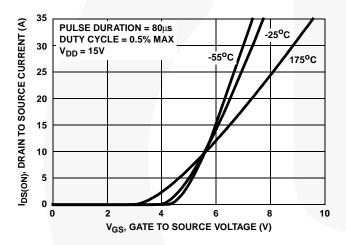


FIGURE 8. TRANSFER CHARACTERISTICS

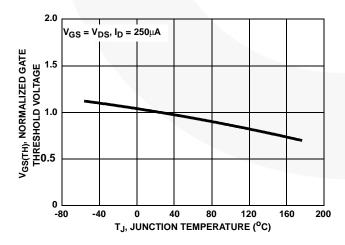


FIGURE 10. NORMALIZED GATE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE

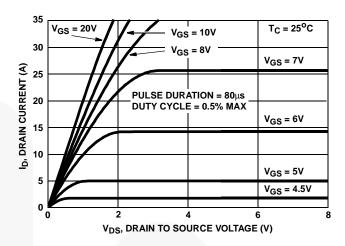


FIGURE 7. SATURATION CHARACTERISTICS

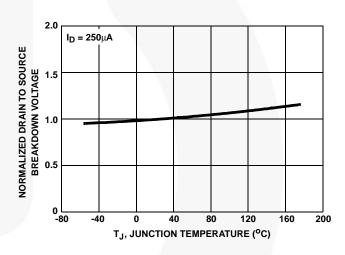


FIGURE 9. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

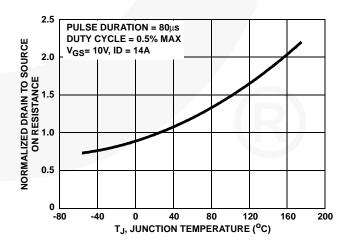


FIGURE 11. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

Typical Performance Curves Unless Otherwise Specified (Continued)

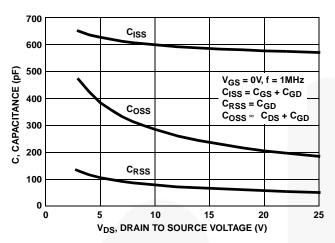
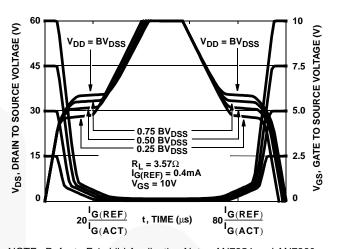


FIGURE 12. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE



NOTE: Refer to Fairchild Application Notes AN7254 and AN7260,
FIGURE 13. NORMALIZED SWITCHING WAVEFORMS FOR
CONSTANT CURRENT GATE DRIVE

Test Circuits and Waveforms

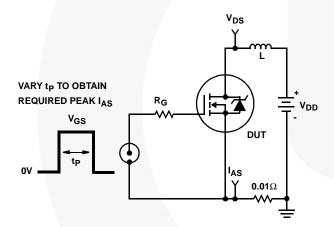


FIGURE 14. UNCLAMPED ENERGY TEST CIRCUIT

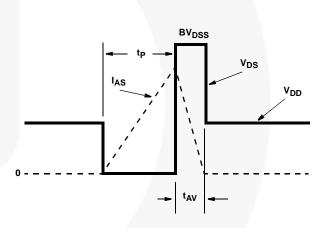


FIGURE 15. UNCLAMPED ENERGY WAVEFORMS

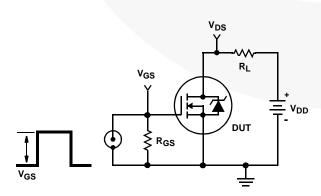


FIGURE 16. SWITCHING TIME TEST CIRCUIT

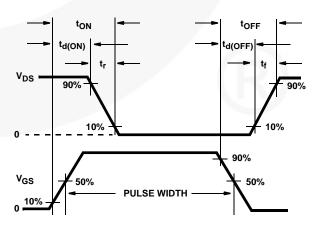
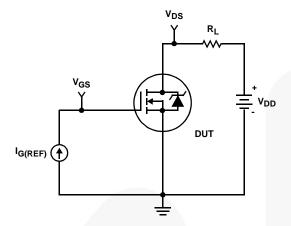


FIGURE 17. RESISTIVE SWITCHING WAVEFORMS

Test Circuits and Waveforms (Continued)





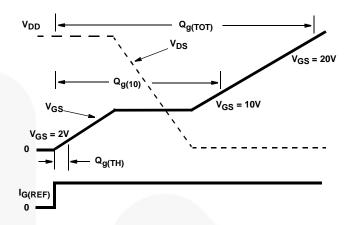


FIGURE 19. GATE CHARGE WAVEFORMS

PSPICE Electrical Model

```
.SUBCKT RFD14N05 2 1 3 :
                                rev 9/12/94
CA 12 8 8.84e-10
CB 15 14 9.34e-10
                                                                    DPLCAP
CIN 6 8 5.2e-10
                                                                                                                 DRAIN
                                                             10
                                                                                                        LDRAIN
DBODY 7 5 DBDMOD
DBREAK 5 11 DBKMOD
                                                                                RSCL1
DPLCAP 10 5 DPLCAPMOD
                                                                                        DBREAK
                                                                  RSCL2
                                                                                 51
                                                                              <u>5</u>
51
EBREAK 11 7 17 18 62.87
                                                                                 ESCL
EDS 14 8 5 8 1
                                                                                50
EGS 13 8 6 8 1
                                                                                                         DBODY
                                                                                RDRAIN
                                                         ESG
ESG 6 10 6 8 1
                                                                           16
                                                                                        EBREAK(
EVTO 20 6 18 8 1
                                                                      VTO
                                                                       4HF
                                                                                 21 |
                                                                                        MOS<sub>2</sub>
                                                        EVTO
                                    GATE
IT 8 17 1
                                                                  6
                                                   20
                                                         18
8
                                                                               MOS1
                                        LGATE RGATE
LDRAIN 2 5 1e-9
                                                                 RIN≶
LGATE 1 9 4.34e-9
                                                                          CIN
                                                                                                        LSOURCE
LSOURCE 3 7 3.79e-9
                                                                                        RSOURCE
                                                                                  8
                                                                                                         -m—o 3
SOURCE
MOS1 16 6 8 8 MOSMOD M = 0.99
MOS2 16 21 8 8 MOSMOD M = 0.01
                                                         S1A
                                                                 S2A
                                                                                                  RBREAK
                                                                       15
                                                           13
                                                                  14
13
RBREAK 17 18 RBKMOD 1
                                                                                                            18
                                                           8
RDRAIN 50 16 RDSMOD 2.2e-3
                                                         S1B P
                                                                 PS2B
                                                                                                            RVTO
RGATE 9 20 5.64
                                                                  13
RIN 6 8 1e9
                                                                                                            19
                                                                         СВ
                                                       CA
                                                                                                    IT
RSCL1 5 51 RSCLMOD 1e-6
                                                                                                              VRAT
RSCL2 5 50 1e3
                                                                 8
                                                                             8
                                                                       EDS (
                                                           EGS
RSOURCE 8 7 RDSMOD 42.3e-3
RVTO 18 19 RVTOMOD 1
S1A 6 12 13 8 S1AMOD
S1B 13 12 13 8 S1BMOD
S2A 6 15 14 13 S2AMOD
S2B 13 15 14 13 S2BMOD
VBAT 8 19 DC 1
VTO 21 6 0.82
ESCL 51 50 VALUE = \{(V(5,51)/ABS(V(5,51)))^*(PWR(V(5,51)^*1e6/50,6))\}
.MODEL DBDMOD D (IS = 1.5e-13 RS = 10.9e-3 TRS1 = 2.3e-3 TRS2 = -1.75e-5 CJO = 6.84e-10 TT = 4.2e-8)
.MODEL DBKMOD D (RS = 4.15e-1 TRS1 = 3.73e-3 TRS2 = -3.21e-5)
.MODEL DPLCAPMOD D (CJO = 26.2e-11 IS = 1e-30 N = 10)
.MODEL MOSMOD NMOS (VTO = 3.91 KP = 12.68 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u)
.MODEL RBKMOD RES (TC1 = 7.73e-4 TC2 = 2.12e-6)
.MODEL RDSMOD RES (TC1 = 5.0e-3 TC2 = 2.53e-5)
.MODEL RSCLMOD RES (TC1 = 2.05e-3 TC2 = 1.35e-5)
.MODEL RVTOMOD RES (TC1 = -4.44e-3 TC2 = -6.45e-6)
.MODEL S1AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -5.29 VOFF= -3.29)
.MODEL S1BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -3.29 VOFF= -5.29)
.MODEL S2AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -2.25 VOFF= 2.75)
.MODEL S2BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = 2.75 VOFF= -2.25)
```

ENDS

NOTE: For further discussion of the PSPICE model, consult **A New PSPICE Sub-circuit for the Power MOSFET Featuring Global Temperature Options**; written by William J. Hepp and C. Frank Wheatley.

RFD14N05SM9A



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